

C1  
B1  
long  
forming scribe lanes in the semiconductor substrate, said scribe lanes defining chip formation areas and containing only the semiconductor substrate;

forming a deep well area in each chip formation area, each deep well area having a second conductivity type opposite the first conductivity type; and

forming at least one well area within the deep well area;

D1  
B2  
7. (Twice Amended) The method of claim 5, wherein, the first conductivity type is a p-type conductor; and the second conductivity type is a n-type conductor.

sub C2  
8. (Twice Amended) The method of claim 5, wherein, the first conductivity type is a n-type conductor; and the second conductivity type is a p-type conductor.

sub C3  
B3  
10. (Twice Amended) A method for manufacturing a semiconductor device comprising:

preparing a semiconductor substrate of a first conductivity type;

forming scribe lanes in the semiconductor substrate, said scribe lanes defining chip formation areas;

*C3*  
forming a deep well area in each chip formation area, each deep well area having a second conductivity type opposite the first conductivity type; and

*B3 comp*  
wherein a first conductive well area and a second conductive well area are separately formed within the deep well area,

the first conductive well area is formed of the first conductivity type, and

the second conductive well area is formed of the second conductivity type.

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